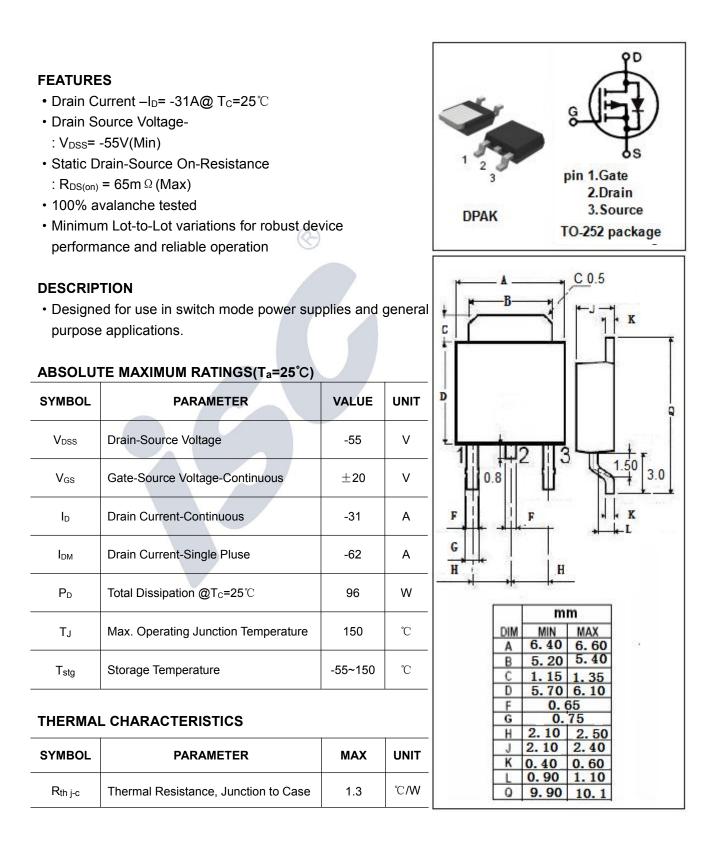


# isc P-Channel MOSFET Transistor

### HLP5305





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## HLP5305

### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = -250uA	-55		V
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> = -250uA	-1.0	-2.5	V
$R_{\text{DS(on)}}$	Drain-Source On-Resistance	V <sub>GS</sub> = -10V; I <sub>D</sub> = -15A		65	mΩ
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0		±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -55V; V <sub>GS</sub> = 0		-1	μA
V <sub>SD</sub>	Forward On-Voltage	I <sub>S</sub> = -15A; V <sub>GS</sub> = 0		-1.5	V

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